NSN 5962-01-291-5011

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-291-5011

view Offilite at https://aerobasegroup.com/hsh/5502-01-251-5011
Body Length:
Between 0.540 inches and 0.560 inches
Body Width:
Between 0.540 inches and 0.560 inches
Body Height:
Between 0.060 inches and 0.120 inches
Maximum Power Dissipation Rating:
1.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Electrostatic sensitive and hermetically sealed and burn in and bidirectional and w/enable
Inclosure Material:
Ceramic
Inclosure Configuration:
Leadless flat pack
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Input Circuit Pattern:
26 input
Case Outline Source And Designator:
C-12 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
7.0 volts power source
Time Rating Per Chacteristic:
55.00 nanoseconds propagation delay time, low to high level output and 55.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Ram
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
32 leadless
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:

Yes - demil/mli

NSN 5962-01-291-5011

Memory Microcircuit - Page 2 of 2



Fiig:

A458a0